



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

MMBT4401LT1 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.6 A

Collector-base voltage

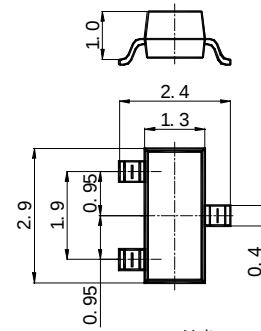
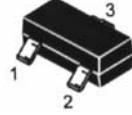
$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=35V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE}=1V, I_C=150mA$	100	300	
	$H_{FE(2)}$	$V_{CE}=2V, I_C=500mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=150mA, I_B=15mA$		0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=150mA, I_B=15mA$		0.95	V
Transition frequency	f_T	$V_{CE}=10V, I_C=20mA$ $f=100MHz$	250		MHz

DEVICE MARKING

:MMBT4401LT1=2X